



Schottky Barrier Diode 1N5817 1N5818 1N5819 DO-41



Specifications

DIP Schottky Barrier Diode 1N5817 1N5818 1N5819 DO-41 in DO-41 package
 Schottky Diodes 1N5819 1A 40V /DO-41
 1.Low power loss, high efficiency.
 2.High current capability, Low VF.

1N5817 - 1N5819
 1.0 AMP. Schottky Barrier Rectifiers

Features

- ✦ Low power loss, high efficiency.
- ✦ High current capability, Low VF.
- ✦ High reliability
- ✦ High surge current capability.
- ✦ Epitaxial construction.
- ✦ Guard-ring for transient protection.
- ✦ For use in low voltage, high frequency inverter, free wheeling, and polarity protection application.

Mechanical Data

- ✦ Cases: Molded plastic DO-41
- ✦ Epoxy: UL 94V-0 rate flame retardant
- ✦ Lead: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
- ✦ Polarity: Color band denotes cathode.
- ✦ High temperature soldering guaranteed: 260°C/10 seconds/.375",(9.5mm) lead lengths at 5 lbs., (2.3kg) tension
- ✦ Weight: 0.33 gram

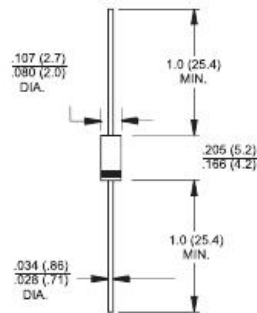
Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%

Type Number	Symbol	1N5817	1N5818	1N5819	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	20	30	40	V
Maximum RMS Voltage	V_{RMS}	14	21	28	V
Maximum DC Blocking Voltage	V_{DC}	20	30	40	V
Maximum Average Forward Rectified Current .375 (9.5mm) Lead Length @ $T_L = 90^\circ C$	$I_{(AV)}$	1.0			A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	25			A
Maximum Instantaneous Forward Voltage @ 1.0A	V_F	0.45	0.550	0.600	V
Maximum Instantaneous Forward Voltage @ 3.0A	V_F	0.750	0.875	0.900	V
Maximum DC Reverse Current @ $T_a=25^\circ C$ at Rated DC Blocking Voltage @ $T_a=125^\circ C$	I_R	1.0 10.0			 mA
Typical Junction Capacitance (Note 2)	C_j	55			pF
Typical Thermal Resistance (Note 1)	$R_{\theta JA}$ $R_{\theta JC}$	100 45			 °C/W
Operating Temperature Range	T_j	-65 to +125			°C
Storage Temperature Range	T_{STG}	-65 to +150			°C

Notes: 1. Mount on Cu-Pad Size 5mm x 5mm on P.C.B.
 2. Measured at 1 MHz and Applied Reverse Voltage of 4.0 V D.C.

DO-41



Dimensions in inches and (millimeters)